

**Modular Optical Wafer Inspection
for High-Speed Quality Control**

CrackScan

100% Detection Rate – Reliable Yield Increase

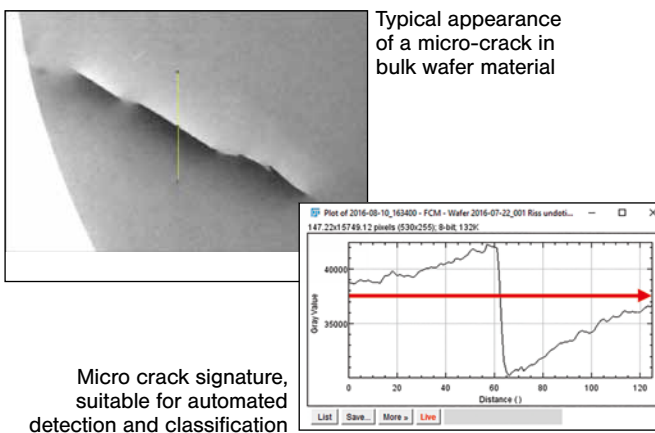
ISRA
VISION

High-Speed Throughput for Su

Compact Design – Small Fo

High-precision inspection in semiconductor electronics – modular optical wafer inspection for micro crack detection

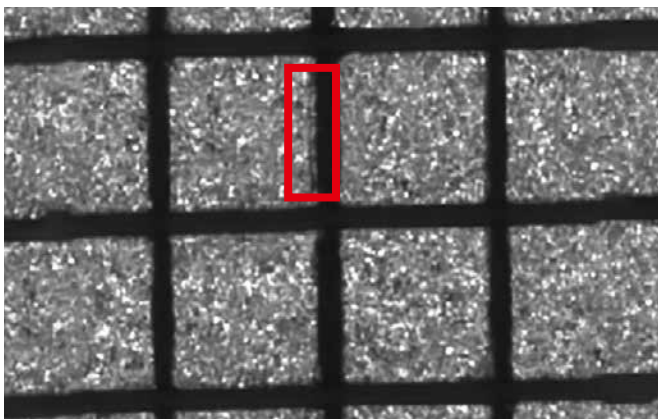
Semiconductor materials, especially compound materials, are known to be brittle and sensitive to cracks. Either introduced during the wafering process, front-end or back-end process, invisible micro cracks pose a high risk of interrupting the process chain, reducing yield or can result in low customer satisfaction when shipping defective parts. ISRA's multiview technology, along with patent pending light coupling into wafer materials, enables a safe, quick and cost efficient way of avoiding those risks.



On bare wafer materials, separated dies on a dicing frame, top or bottom side, also through carrier like foil or substrate: The system detects micro cracks precisely and classifies between cracks, scratches and other defects.

Standardized interfaces according to SEMI standards in hard- and software for fast and reliable integration

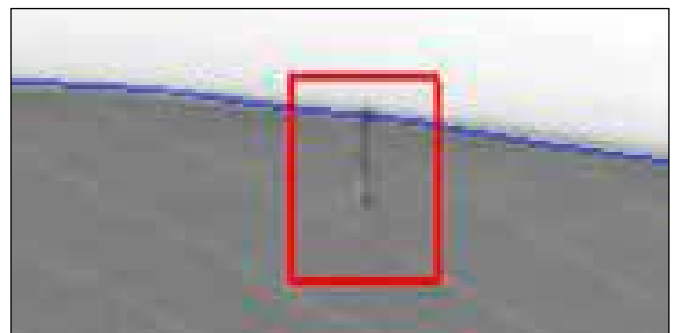
Along with tools for optical layer thickness uniformity and 3D inspection tools, ISRA covers a wide range of semiconductor applications. Available in various configurations, from manual desktop unit up to parallel processing units on wafer handling modules, all throughput requirements can be met.



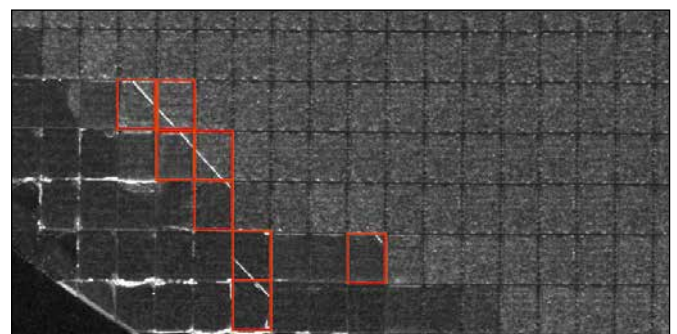
Typical chipping / cracking defect after dicing

Application

- Micro crack detection with $< 5 \mu\text{m}$ crack width
- Suitable for FEOL and BEOL process stages
- Applicable for 75 - 300 mm (3 - 12") wafers
- Multiple cameras allow simultaneous scanning of top and bottom sides
- Works for all wafer materials (Silicon, Perovskites, Sapphire)
- Handles bare & laminated wafers, also after dicing
- Integrated adjustment of thresholds and crack characteristics for sensitive optimization of detection result
- High-speed with image acquisition on-the-fly
- Different illumination modes like bright field, dark field in transmission and reflection mode
- Up to 6 fully synchronized images of one sample
- Data processing with optimized algorithms
- No "over-rejection" due to safeguard regions around crack areas, granting higher yield
- High resolution line scan cameras, with state-of-the-art LED line illumination using different wavelengths, allow capturing several images in one scan



Micro-crack at the wafer edge



Electronic inked dies with detected micro-cracks after dicing process

Substantial Cost Saving Potential

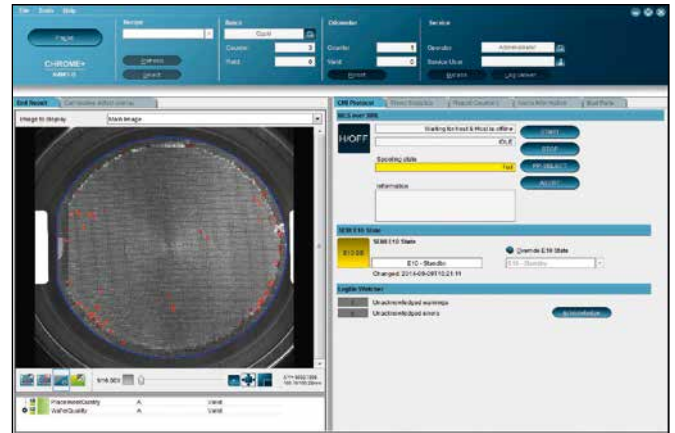
Footprint – Easy to Integrate

Features

- Wafer materials: Si, Sapphire, GaAs, InP, CdTe, LiTa, etc.
- Wafer size: 75 - 300 mm (3 - 12")
- Bare wafers or carrier mounted (e.g. dicing frame)
- Typ. resolution: 20 μm , optional down to 1,5 μm
- Cleanroom class 1000 compatible
- Speed: > 100 WpH with 100% inspection for 8" wafers
- Wafer mapping / 2D coordination map
- Unique and adjustable illumination system
- Motorized XY θ axis system

Benefits at a glance

- Seamless integration into existing process lines
- Detection of natural and artificial micro cracks in high-speed
- Tailor-made optical setup allows significant increase in detection performance
- Flexible integration into high volume wafer handling systems, as well as existing systems
- SEMI-compliant construction for clean room operation in FEOL



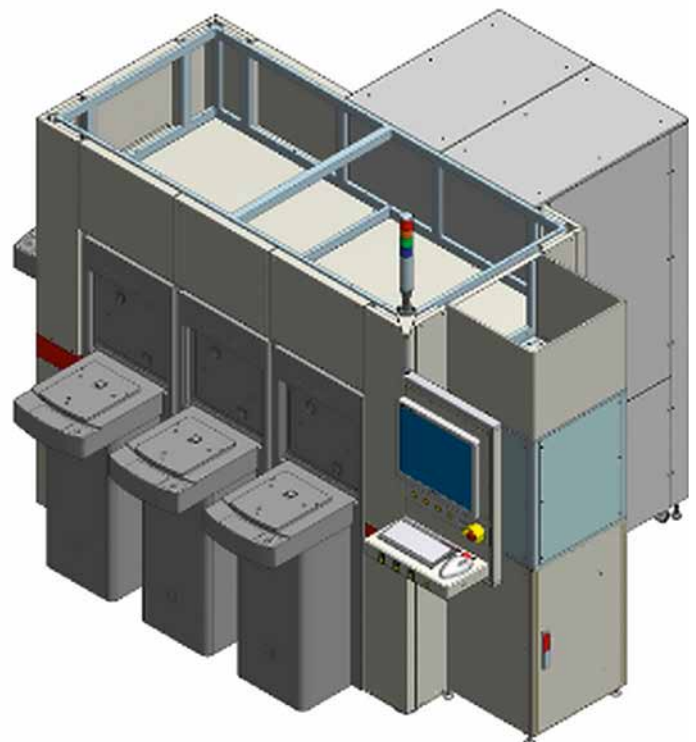
GUI according to SEMI E94 / E95 standard

Options

- Chuck with vacuum fixation for 75 - 300 mm (3 - 12") wafers
- Housing for clean room class 1 (ISO 3)
- IR setup with IR cam & IR illumination
- Granite stand
- DMC / Barcode reader



Manual inspection tool



Possible configuration of a fully automated tool with 2 inspection modules

